

Amendments to the Specification:

Please insert before the first paragraph of the specification:

This application claims priority from PCT Application Serial No. PCT/EP2004/052333, filed September 28, 2004, and German Patent Application No. DE 10348007.2, filed October 15, 2003, both of which are incorporated by reference herein.

In the Abstract:

~~Patterning method, and field effect transistors~~

~~An explanation is given of, inter alia, a~~ patterning method, in which with a filling material (22) with a T-shaped cross section is used as a mask during patterning in order to produce structures having sublithographic dimensions, ~~in particular~~ such as a double-fin field effect transistor.

~~(Figure 1B)~~